

Maurice S Skolnick

List of Publications by Year in descending order

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672
papers

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Strong exciton-photon coupling in an organic semiconductor microcavity. <i>Nature</i> , 1998, 395, 53-55.	13.7	768
2	Angle-Resonant Stimulated Polariton Amplifier. <i>Physical Review Letters</i> , 2000, 84, 1547-1550.	2.9	753
3	Collective fluid dynamics of a polariton condensate in a semiconductor microcavity. <i>Nature</i> , 2009, 457, 291-295.	13.7	494
4	Inverted Electron-Hole Alignment in InAs-GaAs Self-Assembled Quantum Dots. <i>Physical Review Letters</i> , 2000, 84, 733-736.	2.9	467
5	Strong coupling phenomena in quantum microcavity structures. <i>Semiconductor Science and Technology</i> , 1998, 13, 645-669.	1.0	461
6	Observation of a Many-Body Edge Singularity in Quantum-Well Luminescence Spectra. <i>Physical Review Letters</i> , 1987, 58, 2130-2133.	2.9	403
7	Continuous Wave Observation of Massive Polariton Redistribution by Stimulated Scattering in Semiconductor Microcavities. <i>Physical Review Letters</i> , 2000, 85, 3680-3683.	2.9	401
8	Exciton-polaritons in van der Waals heterostructures embedded in tunable microcavities. <i>Nature Communications</i> , 2015, 6, 8579.	5.8	377
9	Room Temperature Polariton Emission from Strongly Coupled Organic Semiconductor Microcavities. <i>Physical Review Letters</i> , 1999, 82, 3316-3319.	2.9	311
10	Persistent currents and quantized vortices in a polariton superfluid. <i>Nature Physics</i> , 2010, 6, 527-533.	6.5	282
11	Improved performance of $1.3\hat{\mu}\text{m}$ multilayer InAs quantum-dot lasers using a high-growth-temperature GaAs spacer layer. <i>Applied Physics Letters</i> , 2004, 85, 704-706.	1.5	267
12	Damping of Exciton Rabi Rotations by Acoustic Phonons in Optically Excited InGaAs Quantum Dots. <i>Physical Review Letters</i> , 2010, 104, 017402.	2.9	258
13	Exciton-light coupling in single and coupled semiconductor microcavities: Polariton dispersion and polarization splitting. <i>Physical Review B</i> , 1999, 59, 5082-5089.	1.1	248
14	Observation of bright polariton solitons in a semiconductor microcavity. <i>Nature Photonics</i> , 2012, 6, 50-55.	15.6	237
15	Parametric oscillation in a vertical microcavity: A polariton condensate or micro-optical parametric oscillation. <i>Physical Review B</i> , 2000, 62, R16247-R16250.	1.1	222
16	Photon-Mediated Hybridization of Frenkel Excitons in Organic Semiconductor Microcavities. <i>Science</i> , 2000, 288, 1620-1623.	6.0	220
17	Chirality of nanophotonic waveguide with embedded quantum emitter for unidirectional spin transfer. <i>Nature Communications</i> , 2016, 7, 11183.	5.8	218
18	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2002, 81, 1708-1710.	1.5	200

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19	Strong exciton-photon coupling in a low-Q all-metal mirror microcavity. Applied Physics Letters, 2002, 81, 3519-3521.	1.5	182
20	Optimizing the growth of 1.3 μm InAs/InGaAs dots-in-a-well structure. Journal of Applied Physics, 2003, 93, 2931-2936.	1.1	180
21	High Purcell factor generation of indistinguishable on-chip single photons. Nature Nanotechnology, 2018, 13, 835-840.	15.6	178
22	Polariton Condensation in Dynamic Acoustic Lattices. Physical Review Letters, 2010, 105, 116402.	2.9	173
23	Phonon-Induced Rabi-Frequency Renormalization of Optically Driven Single InGaAs Quantum Dots. Physical Review Letters, 2010, 105, 177402.	2.9	172
24	Valley-addressable polaritons in atomically thin semiconductors. Nature Photonics, 2017, 11, 497-501.	15.6	169
25	Inversion of exciton level splitting in quantum dots. Physical Review B, 2005, 72, .	1.1	167
26	Electronic energy levels and energy relaxation mechanisms in self-organized InAs/GaAs quantum dots. Physical Review B, 1996, 54, 17738-17744.	1.1	165
27	Charged and neutral exciton complexes in individual self-assembled In(Ga)As quantum dots. Physical Review B, 2001, 63, .	1.1	164
28	Photonic band-structure effects in the reflectivity of periodically patterned waveguides. Physical Review B, 1999, 60, R16255-R16258.	1.1	160
29	Investigation of InGaAs-InP quantum wells by optical spectroscopy. Semiconductor Science and Technology, 1986, 1, 29-40.	1.0	158
30	Long lifetimes of quantum-dot intersublevel transitions in the terahertz range. Nature Materials, 2009, 8, 803-807.	13.3	157
31	Emission spectra and mode structure of InAs/GaAs self-organized quantum dot lasers. Applied Physics Letters, 1998, 73, 969-971.	1.5	152
32	Motional Narrowing in Semiconductor Microcavities. Physical Review Letters, 1996, 77, 4792-4795.	2.9	148
33	Relaxation bottleneck and its suppression in semiconductor microcavities. Physical Review B, 2000, 62, R2283-R2286.	1.1	147
34	Intrinsic Decoherence Mechanisms in the Microcavity Polariton Condensate. Physical Review Letters, 2008, 101, 067404.	2.9	146
35	Observation of multicharged excitons and biexcitons in a single InGaAs quantum dot. Physical Review B, 2001, 63, .	1.1	142
36	High-performance three-layer 1.3- μm InAs-GaAs quantum-dot lasers with very low continuous-wave room-temperature threshold currents. IEEE Photonics Technology Letters, 2005, 17, 1139-1141.	1.3	136

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37	New physics and devices based on self-assembled semiconductor quantum dots. Journal Physics D: Applied Physics, 2005, 38, 2059-2076.	1.3	135
38	Fast Optical Preparation, Control, and Readout of a Single Quantum Dot Spin. Physical Review Letters, 2008, 100, 197401.	2.9	133
39	Resonant coupling of near-infrared radiation to photonic band structure waveguides. Journal of Lightwave Technology, 1999, 17, 2050-2057.	2.7	131
40	Two-Dimensional Metal-Chalcogenide Films in Tunable Optical Microcavities. Nano Letters, 2014, 14, 7003-7008.	4.5	129
41	Exciton-Polariton Gap Solitons in Two-Dimensional Lattices. Physical Review Letters, 2013, 111, 146401.	2.9	124
42	Phonon-Assisted Population Inversion of a Single InGaAs Quantum Dot by Pulsed Laser Excitation. Physical Review Letters, 2015, 114, 137401.	2.9	124
43	Nonlinear polaritons in a monolayer semiconductor coupled to optical bound states in the continuum. Light: Science and Applications, 2020, 9, 56.	7.7	124
44	Nuclear Spin Switch in Semiconductor Quantum Dots. Physical Review Letters, 2007, 98, 026806.	2.9	122
45	Long-wavelength light emission and lasing from InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. Applied Physics Letters, 2005, 86, 143108.	1.5	120
46	Exciton Polaritons in a Two-Dimensional Lieb Lattice with Spin-Orbit Coupling. Physical Review Letters, 2018, 120, 097401.	2.9	120
47	Interfacing Spins in an InGaAs Quantum Dot to a Semiconductor Waveguide Circuit Using Emitted Photons. Physical Review Letters, 2013, 110, 037402.	2.9	119
48	Off-branch polaritons and multiple scattering in semiconductor microcavities. Physical Review B, 2001, 64, .	1.1	115
49	Interplay of order and disorder in the optical properties of opal photonic crystals. Physical Review B, 2002, 66, .	1.1	114
50	SELF-ASSEMBLED SEMICONDUCTOR QUANTUM DOTS: Fundamental Physics and Device Applications. Annual Review of Materials Research, 2004, 34, 181-218.	4.3	113
51	Fine structure of charged and neutral excitons in $\text{InAs-Al}_0.6\text{Ga}_{0.4}\text{As}$ quantum dots. Physical Review B, 2002, 66, .	1.1	108
52	Quantum-confined Stark shifts of charged exciton complexes in quantum dots. Physical Review B, 2004, 70, .	1.1	108
53	An investigation of the deep level photoluminescence spectra of $\text{InP}(\text{Mn})$, $\text{InP}(\text{Fe})$, and of undoped InP . Journal of Applied Physics, 1982, 53, 4955-4963.	1.1	105
54	Electric-field and temperature tuning of exciton-photon coupling in quantum microcavity structures. Physical Review B, 1995, 51, 2600-2603.	1.1	104

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55	Intraband relaxation via polaron decay in InAs self-assembled quantum dots. <i>Physical Review B</i> , 2004, 70, .	1.1	101
56	Mode structure of the L3 photonic crystal cavity. <i>Applied Physics Letters</i> , 2007, 90, 241117.	1.5	99
57	Stimulated spin dynamics of polaritons in semiconductor microcavities. <i>Physical Review B</i> , 2002, 65, .	1.1	96
58	Coherent Optical Control of the Spin of a Single Hole in an InAs/GaAs Quantum Dot. <i>Physical Review Letters</i> , 2012, 108, 017402.	2.9	96
59	Experimental study of light emission from strongly coupled organic semiconductor microcavities following nonresonant laser excitation. <i>Physical Review B</i> , 2002, 65, .	1.1	93
60	Direct Measurement of the Hole-Nuclear Spin Interaction in Single InP/GaInP Quantum Dots Using Photoluminescence Spectroscopy. <i>Physical Review Letters</i> , 2011, 106, 027402.	2.9	93
61	Electron-phonon interactions in indium gallium arsenide. <i>Semiconductor Science and Technology</i> , 1987, 2, 329-336.	1.0	91
62	Transition from strong to weak coupling and the onset of lasing in semiconductor microcavities. <i>Physical Review B</i> , 2002, 65, .	1.1	91
63	An investigation of the anisotropy of the valence band of GaAs by cyclotron resonance. <i>Journal of Physics C: Solid State Physics</i> , 1976, 9, 2809-2821.	1.5	90
64	Enhanced phonon-assisted absorption in single InAs/GaAs quantum dots. <i>Physical Review B</i> , 2001, 63, .	1.1	90
65	p-doped $1.3\frac{1}{4}\mu\text{m}$ InAs [*] /GaAs quantum-dot laser with a low threshold current density and high differential efficiency. <i>Applied Physics Letters</i> , 2006, 89, 073113.	1.5	87
66	Electric-field-dependent carrier capture and escape in self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 2000, 77, 4344-4346.	1.5	86
67	Chiral topological photonics with an embedded quantum emitter. <i>Optica</i> , 2020, 7, 1690.	4.8	86
68	Influences of the spacer layer growth temperature on multilayer InAs [*] /GaAs quantum dot structures. <i>Journal of Applied Physics</i> , 2004, 96, 1988-1992.	1.1	85
69	Room-temperature $1.6\frac{1}{4}\mu\text{m}$ light emission from InAs [*] /GaAs quantum dots with a thin GaAsSb cap layer. <i>Journal of Applied Physics</i> , 2006, 99, 046104.	1.1	85
70	Hole mass measurement in p-type InP and GaP by submillimetre cyclotron resonance in pulsed magnetic fields. <i>Solid State Communications</i> , 1974, 15, 693-697.	0.9	83
71	Highly nonlinear trion-polaritons in a monolayer semiconductor. <i>Nature Communications</i> , 2020, 11, 3589.	5.8	83
72	Spin Textures of Exciton-Polaritons in a Tunable Microcavity with Large TE-TM Splitting. <i>Physical Review Letters</i> , 2015, 115, 246401.	2.9	82

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73	Photoluminescence, photoluminescence excitation, and resonant Raman spectroscopy of disordered and ordered Ga _{0.52} In _{0.48} P. <i>Journal of Applied Physics</i> , 1993, 73, 5163-5172.	1.1	81
74	Far infrared photoconductivity from majority and minority impurities in high purity Si and Ge. <i>Solid State Communications</i> , 1974, 15, 1403-1408.	0.9	80
75	Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. <i>Physical Review B</i> , 1990, 41, 10754-10766.	1.1	80
76	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , 2000, 62, 16784-16791.	1.1	80
77	Rotation of the plane of polarization of light in a semiconductor microcavity. <i>Physical Review B</i> , 2006, 73, .	1.1	79
78	Electroluminescence from a conjugated polymer microcavity structure. <i>Applied Physics Letters</i> , 1995, 67, 1355-1357.	1.5	78
79	Effect of thermal annealing and strain engineering on the fine structure of quantum dot excitons. <i>Physical Review B</i> , 2004, 70, .	1.1	78
80	Optical properties of undoped organometallic grown ZnSe and ZnS. <i>Journal of Crystal Growth</i> , 1982, 59, 301-306.	0.7	77
81	Tailoring of internal fields in InGaAs/GaAs multiwell structures grown on (111)B GaAs. <i>Applied Physics Letters</i> , 1993, 63, 752-754.	1.5	77
82	Polarization Bistability and Resultant Spin Rings in Semiconductor Microcavities. <i>Physical Review Letters</i> , 2010, 105, 216402.	2.9	77
83	Ultrafast nonlinear response of AlGaAs two-dimensional photonic crystal waveguides. <i>Applied Physics Letters</i> , 2003, 83, 851-853.	1.5	76
84	Dynamics of Coherent and Incoherent Spin Polarizations in Ensembles of Quantum Dots. <i>Physical Review Letters</i> , 2004, 93, 057401.	2.9	76
85	Waveguide Coupled Resonance Fluorescence from On-Chip Quantum Emitter. <i>Nano Letters</i> , 2014, 14, 6997-7002.	4.5	75
86	Ultra-low-power hybrid light-matter solitons. <i>Nature Communications</i> , 2015, 6, 8317.	5.8	74
87	Photoluminescence decay time measurements from self-organized InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , 1999, 86, 2555-2561.	1.1	73
88	Comparative study of InGaAs quantum dot lasers with different degrees of dot layer confinement. <i>Applied Physics Letters</i> , 2002, 81, 1-3.	1.5	72
89	InGaAs-InP multiple quantum wells grown by atmospheric pressure metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1987, 51, 24-26.	1.5	71
90	Donor discrimination and bound exciton spectra in InP. <i>Journal of Applied Physics</i> , 1983, 54, 346-359.	1.1	70

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91	Free-carrier screening of the interaction between excitons and longitudinal-optical phonons in In _x Ga _{1-x} As-InP quantum wells. <i>Physical Review B</i> , 1987, 35, 5925-5928.	1.1	70
92	Phonon coupling and X [∓] mixing in GaAs-AlAs short-period superlattices. <i>Physical Review B</i> , 1989, 39, 11191-11194.	1.1	70
93	Element-sensitive measurement of the hole nuclear spin interaction in quantum dots. <i>Nature Physics</i> , 2013, 9, 74-78.	6.5	70
94	Strongly polarized bound exciton luminescence from GaAs grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1985, 46, 427-429.	1.5	68
95	Experimental determination of intervalley transfer mechanisms in GaAs/AlAs heterostructures. <i>Physical Review B</i> , 1996, 54, R8329-R8332.	1.1	68
96	Asymmetric angular emission in semiconductor microcavities. <i>Physical Review B</i> , 2000, 62, R13278-R13281.	1.1	68
97	Coexisting nonequilibrium condensates with long-range spatial coherence in semiconductor microcavities. <i>Physical Review B</i> , 2009, 80, .	1.1	67
98	Cavity-polariton dispersion and polarization splitting in single and coupled semiconductor microcavities. <i>Physics of the Solid State</i> , 1999, 41, 1223-1238.	0.2	66
99	Electroluminescence emission from polariton states in GaAs-based semiconductor microcavities. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	66
100	Valley coherent exciton-polaritons in a monolayer semiconductor. <i>Nature Communications</i> , 2018, 9, 4797.	5.8	66
101	Optical and capacitance spectroscopy of InP:Fe. <i>Journal of Physics C: Solid State Physics</i> , 1981, 14, 5069-5079.	1.5	65
102	Structural analysis of strained quantum dots using nuclear magnetic resonance. <i>Nature Nanotechnology</i> , 2012, 7, 646-650.	15.6	65
103	Hybrid organic-inorganic exciton-polaritons in a strongly coupled microcavity. <i>Physical Review B</i> , 2006, 74, .	1.1	64
104	Photoluminescence study of the density-of-states between Landau levels in the quantum hall effect system. <i>Solid State Communications</i> , 1988, 67, 637-641.	0.9	63
105	Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. <i>Solid-State Electronics</i> , 1989, 32, 1101-1108.	0.8	63
106	Heavy photon dispersions in photonic crystal waveguides. <i>Applied Physics Letters</i> , 2000, 77, 178-180.	1.5	63
107	Electronic band structure of AlGaInP grown by solid-source molecular beam epitaxy. <i>Applied Physics Letters</i> , 1994, 65, 213-215.	1.5	62
108	Manipulation of the homogeneous linewidth of an individual In(Ga)As quantum dot. <i>Physical Review B</i> , 2002, 66, .	1.1	61

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109	Individual neutral and charged In _x Ga _{1-x} As quantum dots with strong in-plane optical anisotropy. <i>Physical Review B</i> , 2005, 72, .	1.1	61
110	Pumping of Nuclear Spins by Optical Excitation of Spin-Forbidden Transitions in a Quantum Dot. <i>Physical Review Letters</i> , 2010, 104, 066804.	2.9	61
111	Dark Solitons in High Velocity Waveguide Polariton Fluids. <i>Physical Review Letters</i> , 2017, 119, 097403.	2.9	61
112	Excited states and selection rules in self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , 1999, 60, R2185-R2188.	1.1	60
113	Continuum transitions and phonon coupling in single self-assembled Stranski-Krastanow quantum dots. <i>Physical Review B</i> , 2003, 68, .	1.1	59
114	Vacuum Rabi coupling enhancement and Zeeman splitting in semiconductor quantum microcavity structures in a high magnetic field. <i>Physical Review B</i> , 1996, 53, R10469-R10472.	1.1	58
115	Effect of Interactions on Vortices in a Nonequilibrium Polariton Condensate. <i>Physical Review Letters</i> , 2010, 104, 126402.	2.9	58
116	Optically induced splitting of bright excitonic states in coupled quantum microcavities. <i>Physical Review B</i> , 1998, 57, 14877-14881.	1.1	57
117	Suppression of Zeeman Splitting of the Energy Levels of Exciton-Polariton Condensates in Semiconductor Microcavities in an External Magnetic Field. <i>Physical Review Letters</i> , 2011, 106, 257401.	2.9	57
118	Fermi-energy-edge singularity in quantum wells containing more than one occupied subband. <i>Physical Review B</i> , 1991, 43, 7354-7357.	1.1	56
119	Many body shakeup in quantum well luminescence spectra. <i>Physical Review Letters</i> , 1993, 70, 3115-3118.	2.9	56
120	Suppressed Polariton Scattering in Semiconductor Microcavities. <i>Physical Review Letters</i> , 1998, 81, 661-664.	2.9	55
121	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , 2003, 82, 3758-3760.	1.5	55
122	Self-organization of multiple polariton-polariton scattering in semiconductor microcavities. <i>Physical Review B</i> , 2008, 77, .	1.1	55
123	Exciton polaritons in semiconductor waveguides. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	54
124	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. <i>Nature Communications</i> , 2015, 6, 6348.	5.8	54
125	Polariton-induced optical asymmetry in semiconductor microcavities. <i>Physical Review B</i> , 1998, 58, 15367-15370.	1.1	53
126	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. <i>Physical Review B</i> , 2008, 78, .	1.1	53

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127	Direct observation of fine structure in the concentration of the deep donor [EL2] and its correlation with dislocations in undoped, semi-insulating GaAs. Journal of Applied Physics, 1984, 56, 1109-1118.	1.1	50
128	Raman scattering in strongly coupled organic semiconductor microcavities. Physical Review B, 2001, 63, .	1.1	50
129	Mode structure of coupled L3 photonic crystal cavities. Optics Express, 2011, 19, 5670.	1.7	50
130	Piezoelectric-field effects on transition energies, oscillator strengths, and level widths in (111)B-grown (In,Ga)As/GaAs multiple quantum wells. Physical Review B, 1993, 48, 8491-8494.	1.1	49
131	Recent progress in polymers for electroluminescence: microcavity devices and electron transport polymers. Thin Solid Films, 1996, 273, 39-47.	0.8	49
132	Band gap of $\tilde{\epsilon}$ -completely disordered $\tilde{\epsilon}$ Ga _{0.52} In _{0.48} P. Applied Physics Letters, 1995, 66, 3185-3187.	1.5	48
133	Polarization-dependent phenomena in the reflectivity spectra of semiconductor quantum microcavities. Physical Review B, 1997, 56, R10032-R10035.	1.1	48
134	Dependence of stimulated scattering in semiconductor microcavities on pump power, angle, and energy. Physical Review B, 2003, 68, .	1.1	48
135	Strong exciton-photon coupling in open semiconductor microcavities. Applied Physics Letters, 2014, 104, .	1.5	48
136	Optical properties of InGaAs $\tilde{\epsilon}$ InP single quantum wells grown by atmospheric pressure metalorganic chemical vapor deposition. Applied Physics Letters, 1986, 48, 1455-1457.	1.5	47
137	Low threshold current density and negative characteristic temperature 1.3 $\tilde{\mu}$ m InAs self-assembled quantum dot lasers. Applied Physics Letters, 2007, 90, 111102.	1.5	47
138	Monolithic integration of a quantum emitter with a compact on-chip beam-splitter. Applied Physics Letters, 2014, 104, .	1.5	47
139	Effects of Spin-Dependent Interactions on Polarization of Bright Polariton Solitons. Physical Review Letters, 2014, 112, 046403.	2.9	47
140	Diamagnetism as a probe of exciton localization in quantum wells. Physical Review B, 1989, 39, 10943-10954.	1.1	46
141	Dominant Effect of Polariton-Polariton Interactions on the Coherence of the Microcavity Optical Parametric Oscillator. Physical Review Letters, 2006, 97, 097402.	2.9	46
142	Photoinduced quenching of infrared absorption nonuniformities of large diameter GaAs crystals. Applied Physics Letters, 1984, 44, 447-449.	1.5	45
143	Ring emission and exciton-pair scattering in semiconductor microcavities. Physical Review B, 2002, 65, .	1.1	45
144	Angular-dependent magnetoluminescence study of the layer compound 2H-PbI ₂ . Physical Review B, 1978, 18, 7080-7088.	1.1	44

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145	Growth and characterisation of quantum wells and selectively doped heterostructures of InP/Ga _{0.47} In _{0.53} As grown by solid source MBE. Journal of Crystal Growth, 1987, 81, 288-295.	0.7	44
146	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. Physical Review B, 1990, 42, 3069-3076.	1.1	44
147	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. Applied Physics Letters, 2008, 92, .	1.5	44
148	Beating of Exciton-Dressed States in a Single Semiconductor $\langle \text{mml:math} \text{xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \rangle \langle \text{mml:mi} \rangle \text{InGaAs} \langle \text{mml:mi} \rangle \langle \text{mml:mo} \rangle / \langle \text{mml:mo} \rangle \langle \text{mml:mi} \rangle \text{GaAs} \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle \text{Quantum Dot. Physical Review Letters, 2009, 102, 207401.}$	2.9	44
149	Optical orientation and control of spin memory in individual InGaAs quantum dots. Physical Review B, 2005, 72, .	1.1	43
150	Magneto-optical studies of self-organized InAs/GaAs quantum dots. Physical Review B, 1998, 57, R2073-R2076.	1.1	42
151	Restoring mode degeneracy in H1 photonic crystal cavities by uniaxial strain tuning. Applied Physics Letters, 2012, 100, .	1.5	42
152	Experimental observation of topological Z2 exciton-polaritons in transition metal dichalcogenide monolayers. Nature Communications, 2021, 12, 4425.	5.8	42
153	Polariton parametric scattering processes in semiconductor microcavities observed in continuous wave experiments. Physical Review B, 2002, 65, .	1.1	41
154	Engineering carrier confinement potentials in 1.3- μ m InAs/GaAs quantum dots with InAlAs layers: Enhancement of the high-temperature photoluminescence intensity. Applied Physics Letters, 2003, 83, 3716-3718.	1.5	41
155	Polarized quantum dot emission from photonic crystal nanocavities studied under moderate resonant enhanced excitation. Optics Express, 2007, 15, 17221.	1.7	41
156	Measurement of the spin temperature of optically cooled nuclei and GaAs hyperfine constants in GaAs/AlGaAs quantum dots. Nature Materials, 2017, 16, 982-986.	13.3	41
157	The complex form of donor energy levels in gallium phosphide. Journal of Physics C: Solid State Physics, 1977, 10, 5111-5129.	1.5	40
158	Time resolved DC electroluminescence studies in ZnS:Mn, Cu powder phosphors. Journal Physics D: Applied Physics, 1981, 14, 301-322.	1.3	40
159	Control of polarized single quantum dot emission in high-quality-factor microcavity pillars. Applied Physics Letters, 2006, 88, 051113.	1.5	40
160	Homogeneous Array of Nanowire-Embedded Quantum Light Emitters. Nano Letters, 2013, 13, 861-865.	4.5	40
161	Properties of the electron-hole liquid in GaP. Physical Review B, 1979, 19, 2231-2245.	1.1	39
162	Electroreflectance spectroscopy from quantum well structures in an electric field. Journal of Physics C: Solid State Physics, 1986, 19, 857-871.	1.5	39

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163	The growth by MOCVD using new group VI sources and assessment by HRTEM and CI of Zn-based II ^{VI} single crystal layers. Journal of Crystal Growth, 1985, 72, 17-22.	0.7	38
164	Nonlinearities in emission from the lower polariton branch of semiconductor microcavities. Physical Review B, 1999, 60, R11293-R11296.	1.1	38
165	Structural and optical studies of vertically aligned InAs/GaAs self-assembled quantum dots. Journal of Applied Physics, 2001, 90, 6374-6378.	1.1	38
166	Polarization conversion in the reflectivity properties of photonic crystal waveguides. IEEE Journal of Quantum Electronics, 2002, 38, 880-884.	1.0	38
167	Transition metal diffusion in InP: Photoluminescence investigation. Journal of Applied Physics, 1984, 55, 2951-2961.	1.1	37
168	Recombination and loss mechanisms in low-threshold InAs-GaAs 1.3- μm quantum-dot lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1041-1047.	1.9	37
169	Whispering gallery resonances in semiconductor micropillars. Applied Physics Letters, 2007, 91, 071115.	1.5	37
170	Linearly Polarized Emission from an Embedded Quantum Dot Using Nanowire Morphology Control. Nano Letters, 2015, 15, 1559-1563.	4.5	37
171	Observation of an Electron-Hole Liquid in Cubic SiC. Physical Review Letters, 1978, 40, 56-60.	2.9	36
172	Identification of donors in vapor grown indium phosphide. Journal of Applied Physics, 1984, 55, 957-963.	1.1	36
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